

Supporting Information

Surface Engineering Based on Ionic Liquids for Efficient and Stable CsPbI₃ Perovskite Solar Cells

Dong Rui,^{a,#} Jianfei Fu,^{b,#} Qiaoyun Chen,^a Ji Cao,^a Wenting Wu,^a Lei Chen,^c Jing Zhang,^c Zelong Zhang,^{a,*} Yi Zhou^{a,*} and Bo Song^{a,*}

^a Laboratory of Advanced Optoelectronic Materials, Suzhou Key Laboratory of Novel Semiconductor-optoelectronics Materials and Devices, College of Chemistry, Chemical Engineering and Materials Science, Soochow University, Suzhou 215123, P. R. China

^b School of Materials Science and Engineering (MSE), NingboTech University, Ningbo, 315211, P. R. China

^c School of Material Science & Engineering, National Experimental Demonstration Center for Materials Science & Engineering, Jiangsu Province Cultivation base for State Key Laboratory of Photovoltaic Science and Technology, Changzhou University,

Changzhou, Jiangsu 213164, P. R. China

[#] Dong Rui and Jianfei Fu contributed equally to this work.

[*] Corresponding authors: songbo@suda.edu.cn (B. Song); yizhou@suda.edu.cn (Y. Zhou); zljzhang@suda.edu.cn (Z. Zhang)

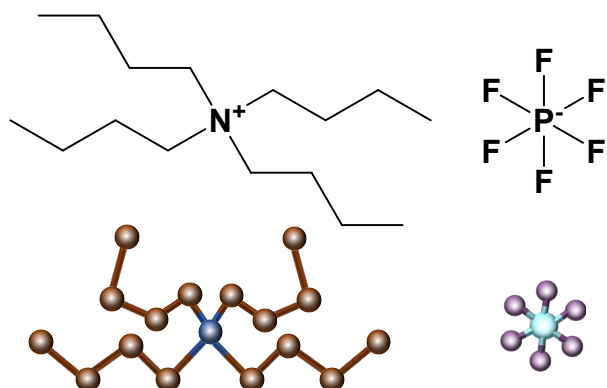


Fig. S1. Chemical structures and corresponding structural diagrams of TBAPF₆.

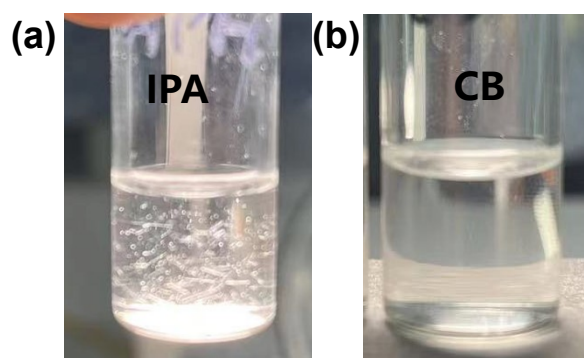


Fig. S2. The solubility of TBAPF₆ in (a) isopropanol and (b) chlorobenzene. According to previous reports, isopropyl alcohol (IPA) and chlorobenzene (CB) were common solvents for Surface treatment of as-deposited CsPbI₃ films and were used in this work.¹⁻³ The same amount of TBAPF₆ was added in equal volume of IPA or CB. After stirring, TBAPF₆ couldn't dissolve in IPA and there was a large amount of precipitation at room temperature. With heating, TBAPF₆ gradually dissolved in IPA and a colorless and transparent solution would be observed. However, crystal particles would precipitate rapidly after cooling down (Fig. S2a). In contrast, TBAPF₆ could well dissolve in CB to form a colorless and transparent solution at room temperature (Fig. S2b).

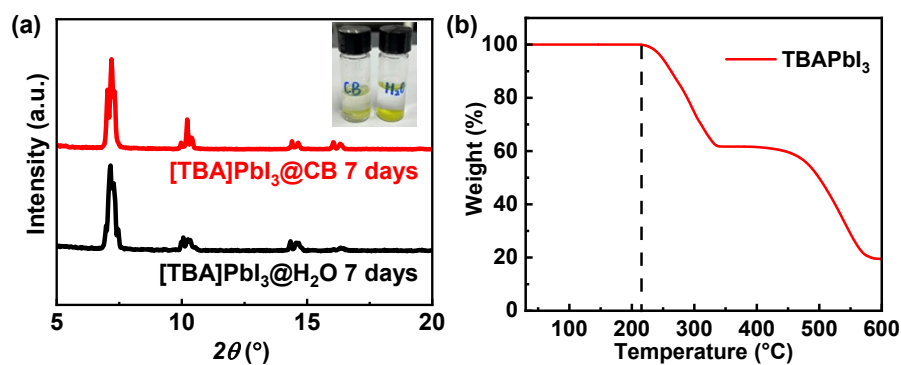


Fig. S3. (a) X-ray diffraction patterns of the [TBA]PbI₃ single crystal immersed in deionized water or CB for 7 days. (b) TGA curve of the low-dimensional material

[TBA]PbI₃.

On one hand, under the consideration of moisture stability of synthetic [TBA]PbI₃ single crystals, [TBA]PbI₃ was immersed in deionized water at room temperature for 7 days. On the other hand, the using of hole transport material (HTM) in this work is Spiro-OMeTAD and CB is the common solvent for Spiro-OMeTAD.⁴⁻⁶ Therefore, the spinning coating of hole transport layer (HTL) could cause damage to perovskite layer, and the similar experiment was conducted by soaking [TBA]PbI₃ into CB. Herein, we used XRD to estimate the degradation of [TBA]PbI₃ single crystals (Fig. S3a).

[TBA]PbI₃ single crystals exhibited excellent thermal stability by thermogravimetric analysis (TGA) measurement. The weight loss of synthetic [TBA]PbI₃ single crystals was only 1 wt% when temperature increased up to 220 °C, and the apparent weight losses happened at temperature ranges from 220 °C to 400 °C and from 400 °C to 600 °C, corresponding to volatilization of TBAI and sublimation of PbI₂, respectively.⁷

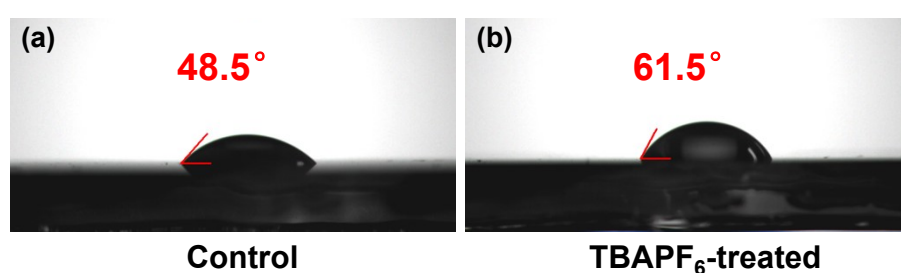


Fig. S4. Water contact angle measurements on the surface of (a) control and (b) TBAPF₆-treated films.

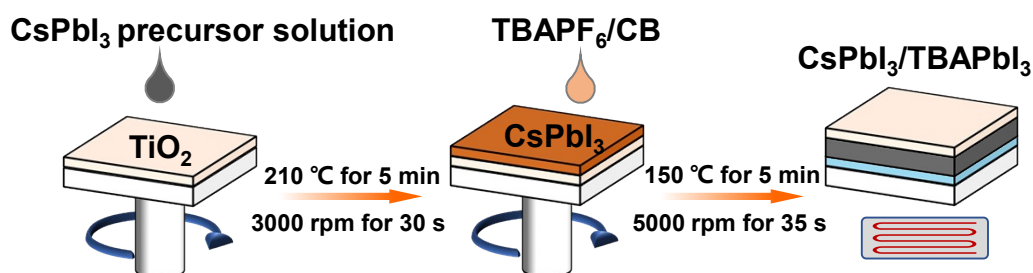


Fig. S5. Schematic diagram of the preparation of CsPbI₃ films with surface treatment of TBAPF₆.

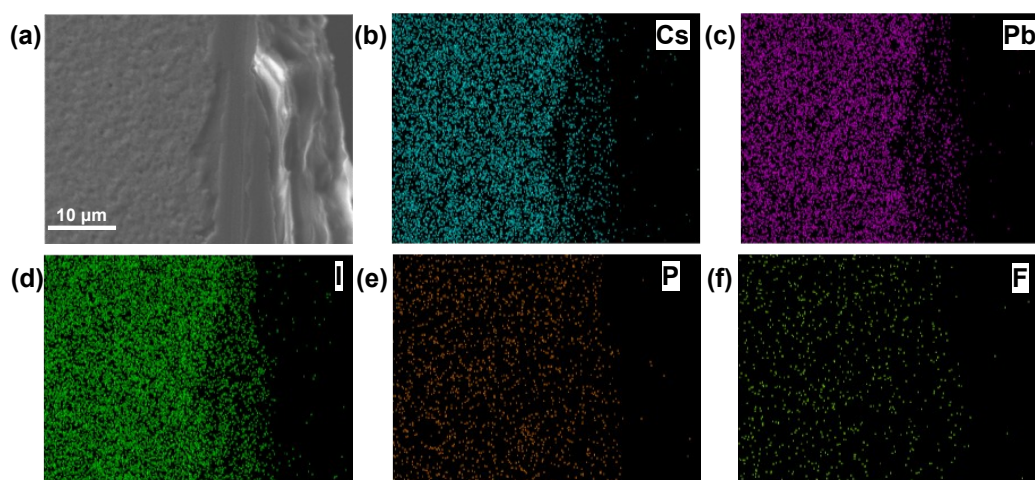


Fig. S6. (a) SEM image of TBAPF₆-treated film, (b-f) Elemental analysis spectra of Cs, Pb, I, P, and F.

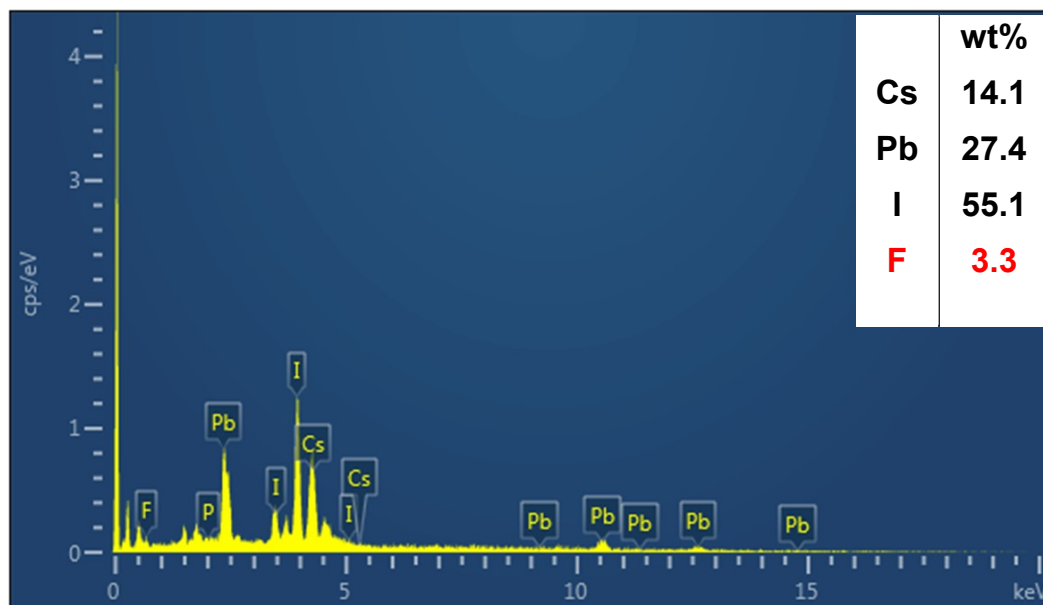


Fig. S7. Relative content analysis results of different elements on the surface of the TBAPF₆-treated film.

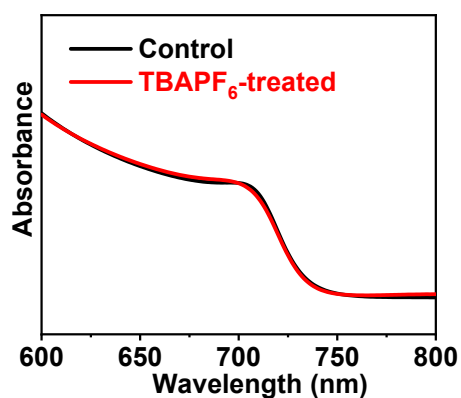


Fig. S8. UV-vis absorption spectra of the control and TBAPF₆-treated films.

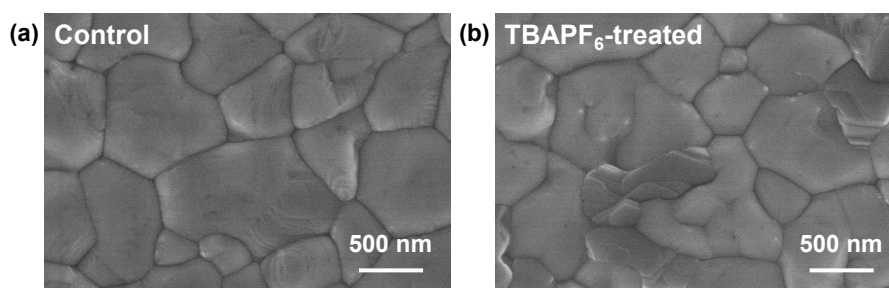


Fig. S9. SEM images of (a) control and (b) TBAPF₆-treated films.

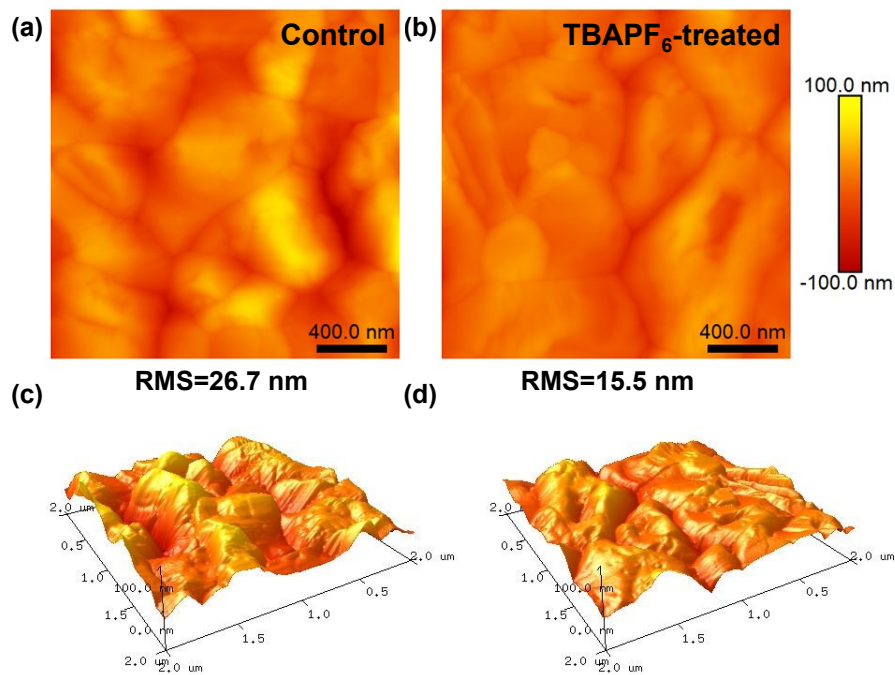


Fig. S10. AFM images of (a), (c) control and (b), (d) TBAPF₆-treated films.

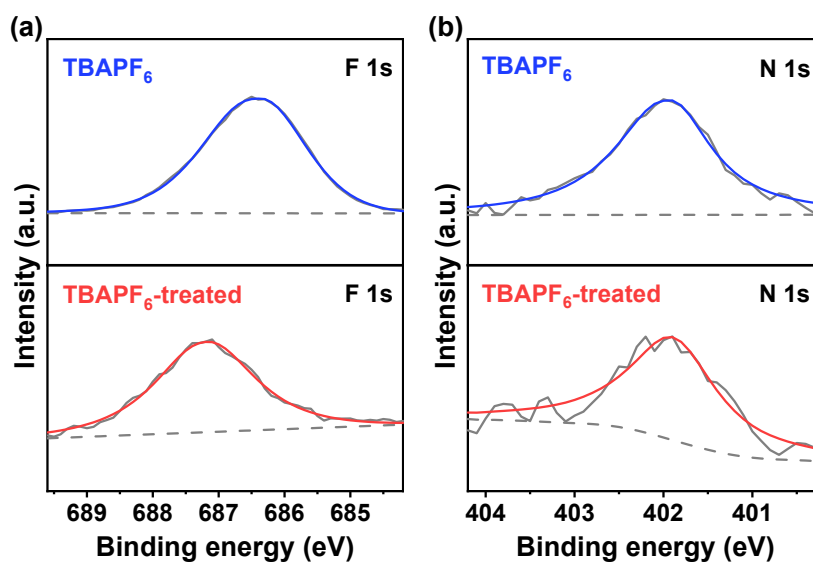


Fig. S11. XPS spectra of TBAPF₆ sample and TBAPF₆-treated films. (a) F 1s, (b) N 1s.

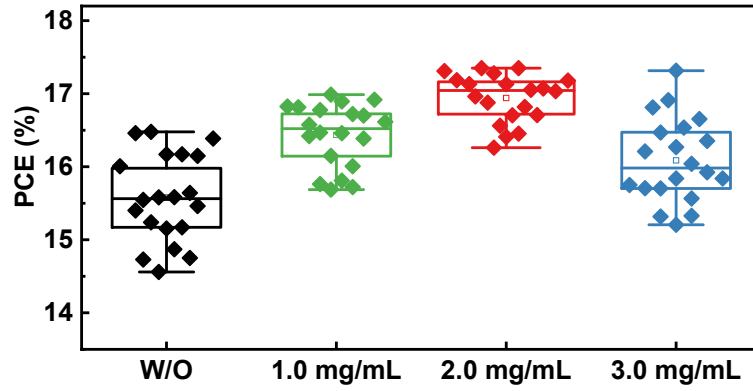


Fig. S12. PCEs statistics of C-PSCs treated with different concentrations of TBAPF₆.

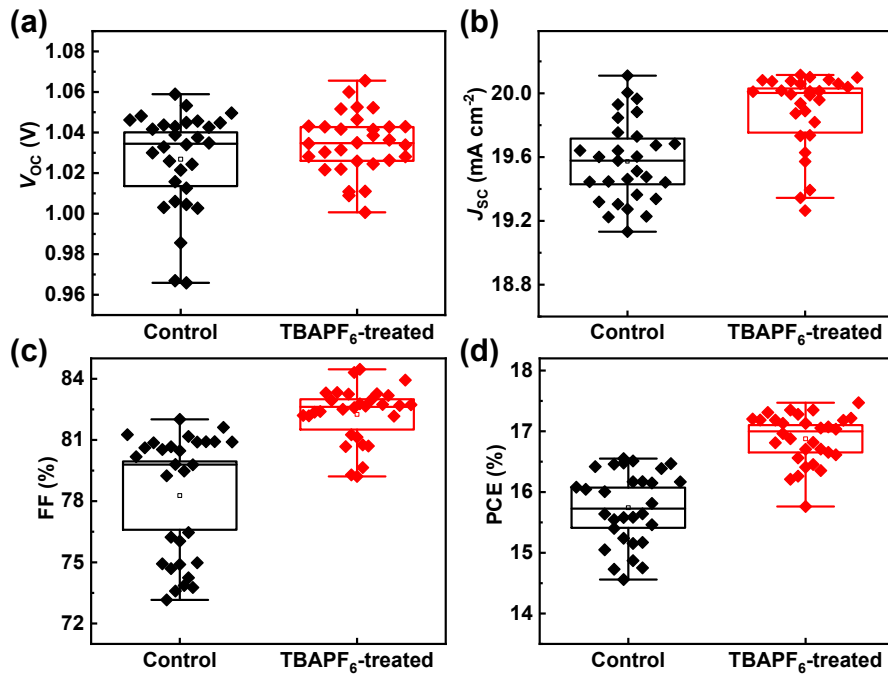


Fig. S13. Histograms of the (a) V_{oc} , (b) J_{sc} , (c) FF, and (d) PCE values based on the control and TBAPF₆-treated devices.

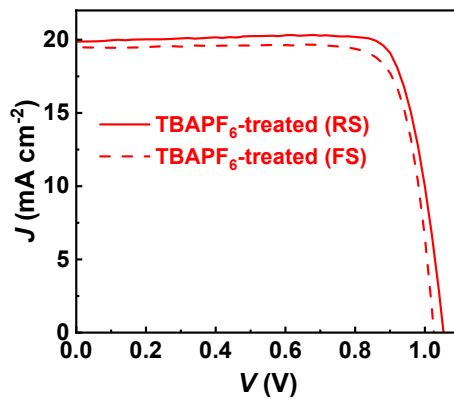


Fig. S14. Reverse scan (RS) and forward scan (FS) of TBAPF₆-treated devices.

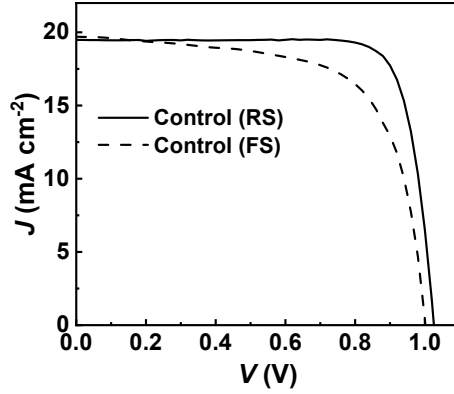


Fig. S15. Reverse scan and forward scan of control devices.

Table S1. Fitted parameters from TRPL spectra for the control and TBAPF₆-treated films.

	τ_1 (ns)	τ_2 (ns)	f_1 (%)	f_2 (%)	τ_{ave} (ns)
Control	2.4	28.2	12.1	87.9	27.9
TBAPF ₆ -treated	2.0	37.5	6.7	93.3	37.3

Table S2. Photovoltaic parameters of the control and TBAPF₆-treated devices.

	V_{OC} (V)	J_{SC} (mA cm) ⁻²	FF (%)	PCE _{best} (PCE _{avg}) (%)
Control	1.03	19.93	80.9	16.55 (15.69 ± 0.86)
TBAPF ₆ -treated	1.06	20.01	82.2	17.47 (16.72 ± 0.75)

Table S3. Photovoltaic parameters of the control and TBAPF₆-treated devices in the reverse scan and forward scan directions.

		V_{OC} (V)	J_{SC} (mA cm) ⁻²	FF (%)	PCE (%)	h^a
Control	RS	1.03	19.48	80.9	16.17	18.6%
	FS	1.00	19.70	66.8	13.17	
TBAPF ₆ -treated	RS	1.05	19.87	83.2	17.41	8.5%
	FS	1.03	19.59	79.2	15.94	

^a $h = (PCE_{RS} - PCE_{FS}) / PCE_{RS}$, where RS and FS represent the reverse and forward scan directions, respectively.

References

1. X. Tan, S. B. Wang, Q. X. Zhang, H. C. Liu, W. P. Li, L. Q. Zhu and H. N. Chen, *Matter*, 2023, **6**, 691-727.
2. X. Zhu, M. Du, J. Feng, H. Wang, Z. Xu, L. Wang, S. Zuo, C. Wang, Z. Wang, C. Zhang, X. Ren, S. Priya, D. Yang and S. Liu, *Angew. Chem. Int. Ed.*, 2021, **60**, 4238-4244.
3. X. Liu, X. Wang, T. Zhang, Y. Miao, Z. Qin, Y. Chen and Y. Zhao, *Angew. Chem. Int. Ed.*, 2021, **60**, 12351-12355.
4. T. Wu, W. X. Ji, L. G. Zhang, Q. Y. Chen, J. F. Fu, J. J. Zhang, Z. L. Zhang, Y. Zhou, B. Dong and B. Song, *J. Mater. Chem. A*, 2023, **11**, 3599-3607.
5. J. F. Fu, J. J. Zhang, T. Y. Zhang, L. G. Yuan, Z. L. Zhang, Z. X. Jiang, Z. Z. Huang, T. Wu, K. Y. Yan, L. G. Zhang, A. L. Wang, W. X. Ji, Y. Zhou and B. Song, *Acs Nano*, 2023, **17**, 2802-2812.
6. X. B. Chu, Q. F. Ye, Z. H. Wang, C. Zhang, F. Ma, Z. H. Qu, Y. Zhao, Z. G. Yin, H. X. Deng, X. W. Zhang and J. B. You, *Nat. Energy*, 2023, **8**, 372-380.
7. Y.-J. She, S.-P. Zhao, Z.-F. Tian and X.-M. Ren, *Inorg. Chem. Commun.*, 2014, **46**, 29-32.